

Characterization of intermediate band materials and solar cells

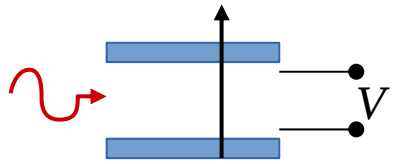


C. del Cañizo

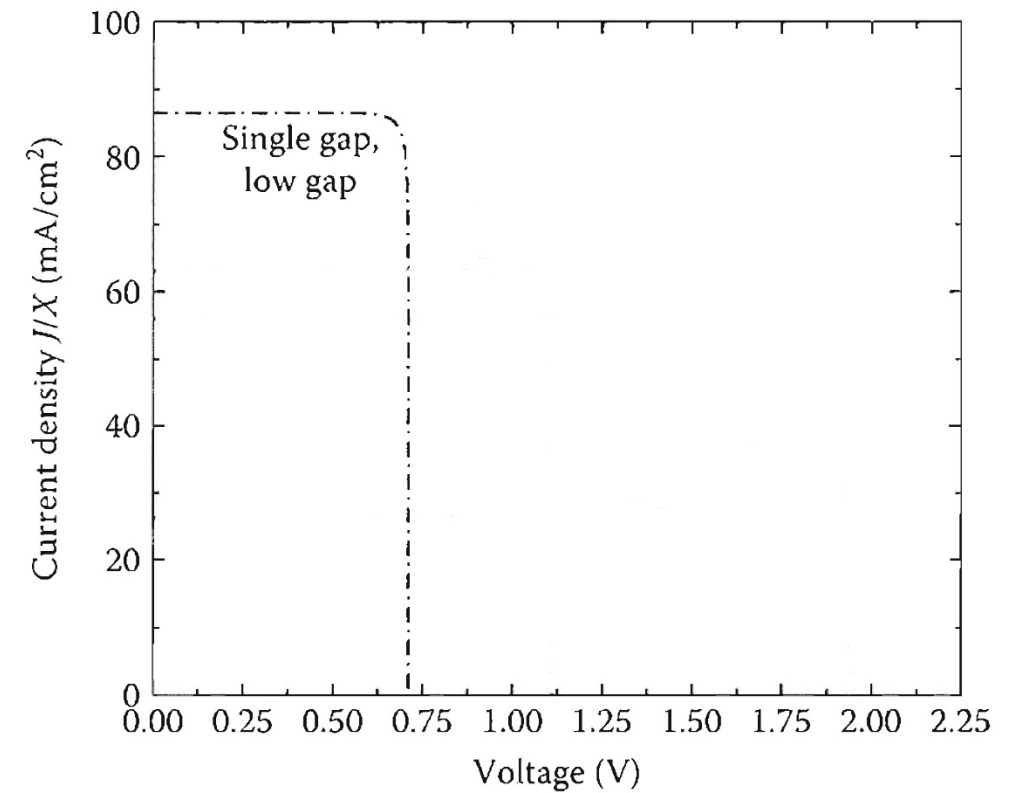
CHEETA Workshop:
Advanced characterization methods for PV
Freiburg, January 14th 2016

- Brief overview of the IB concept
- Two-photon below bandgap absorption characterization
- Voltage preservation
- Characterization of some IB properties

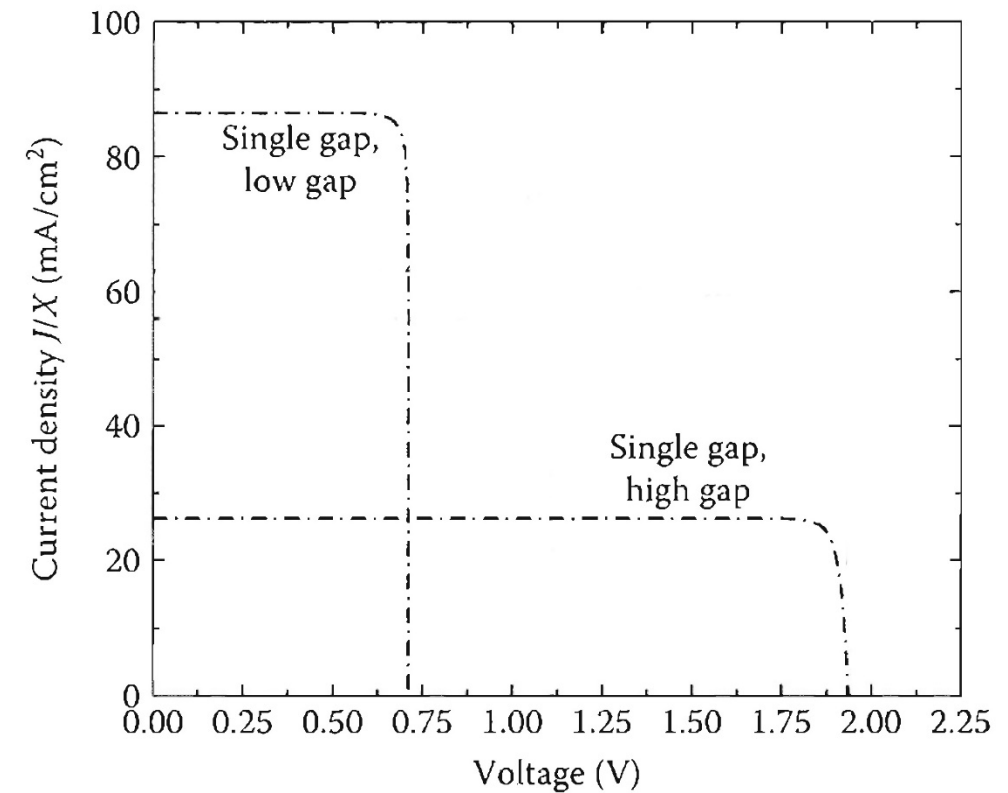
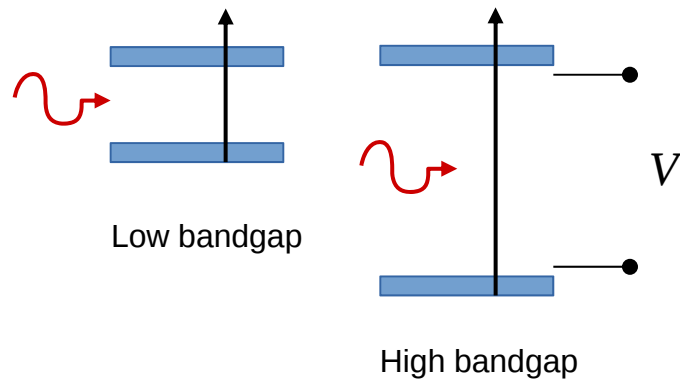
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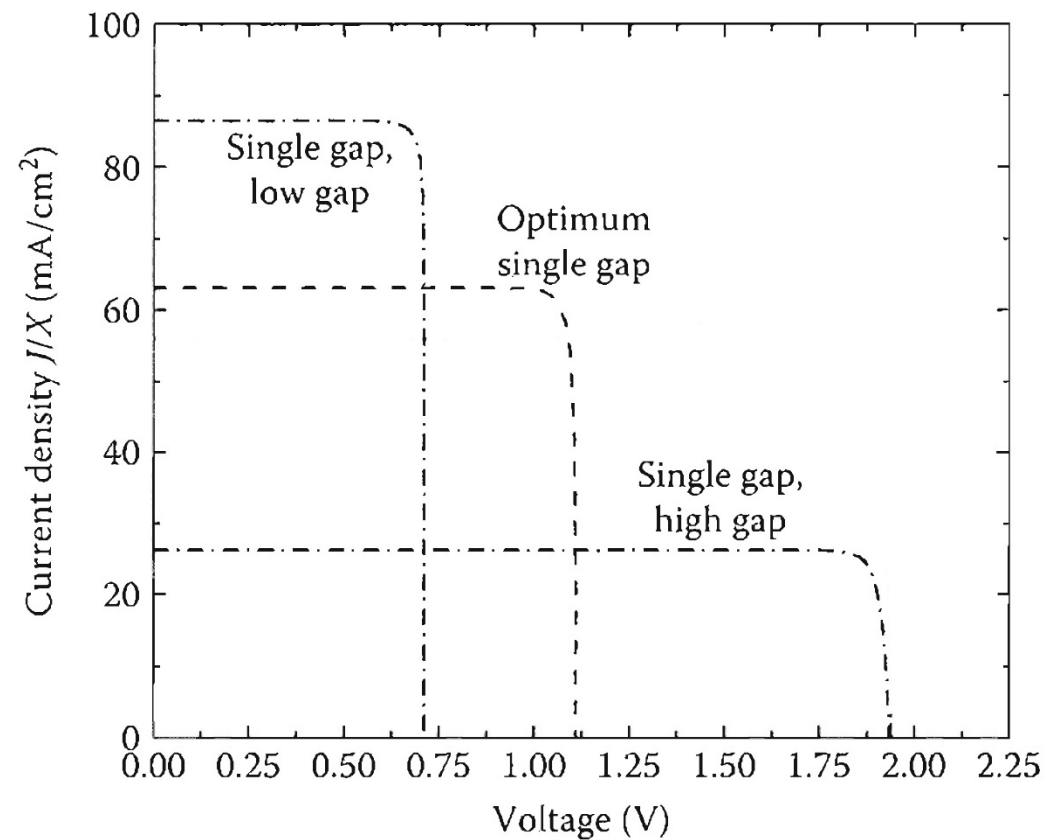
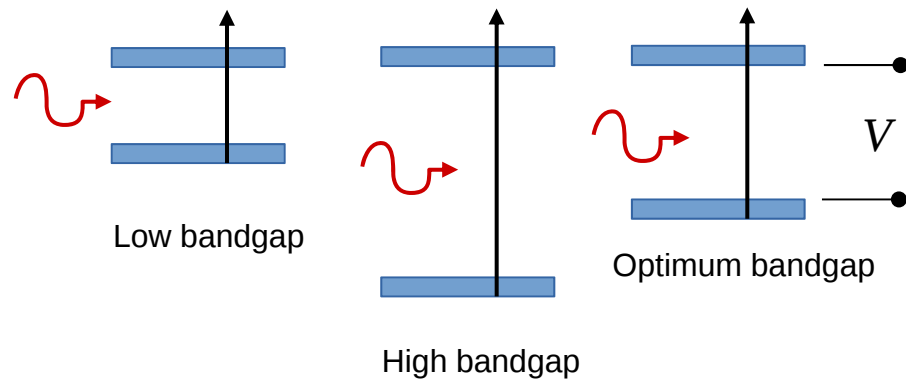
Low bandgap



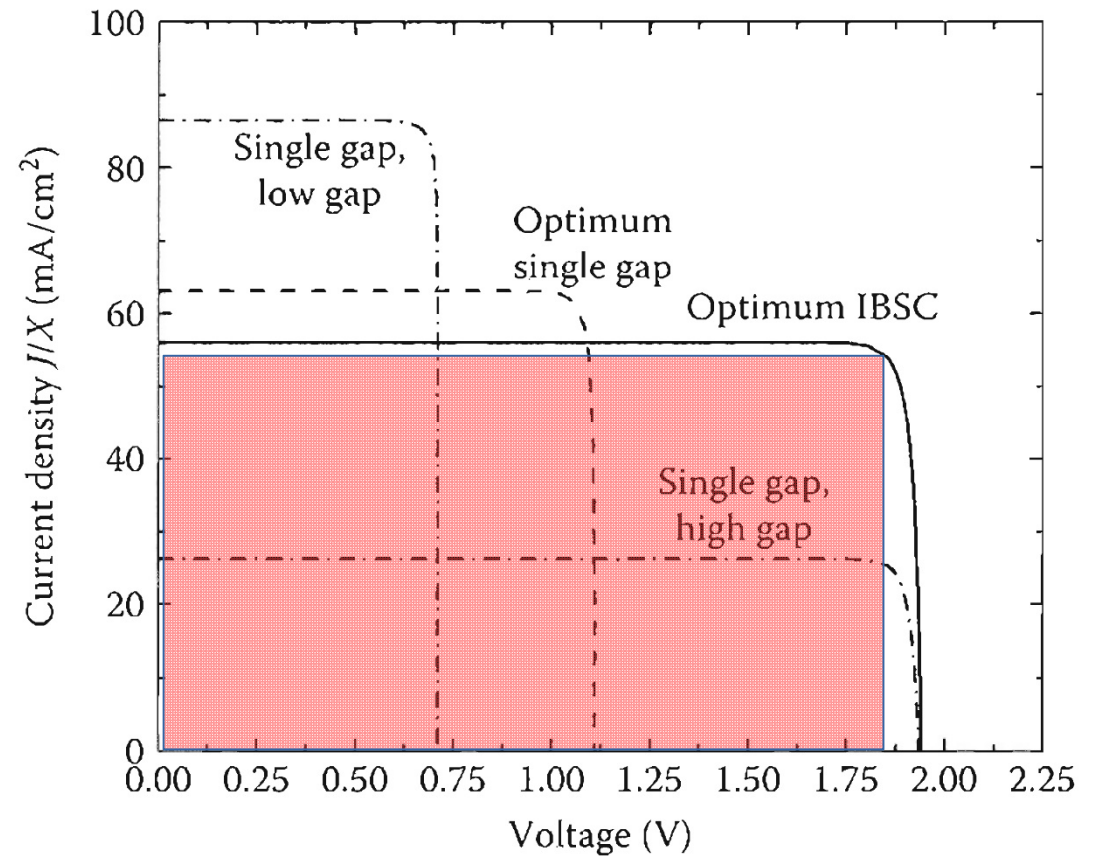
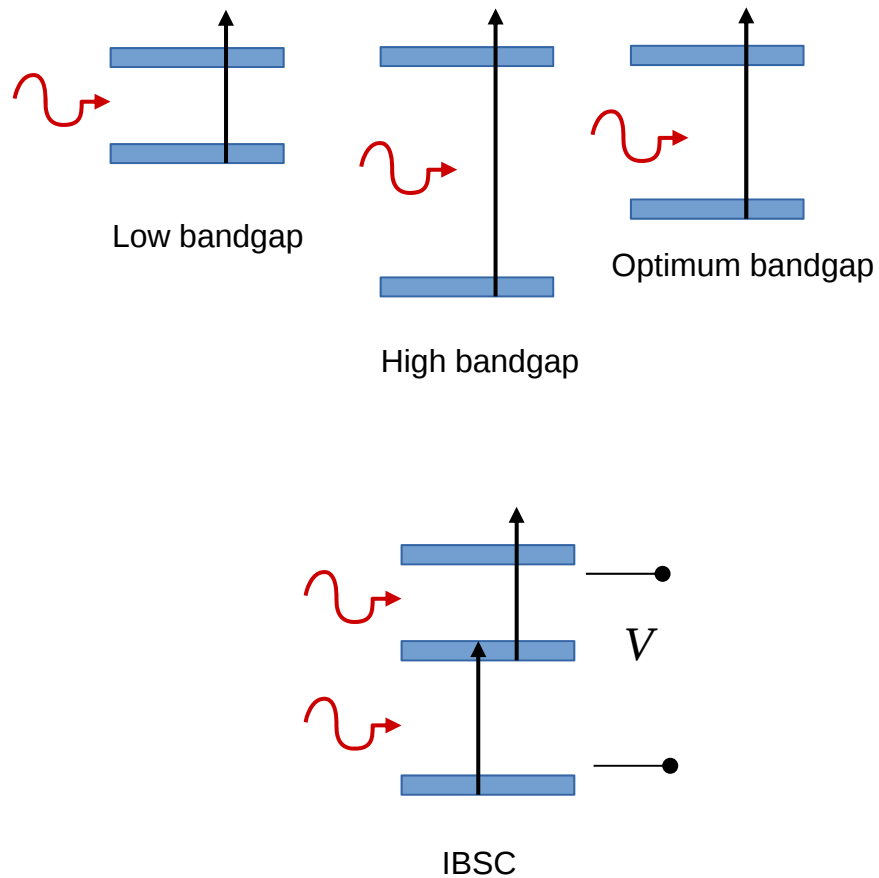
IBSC concept



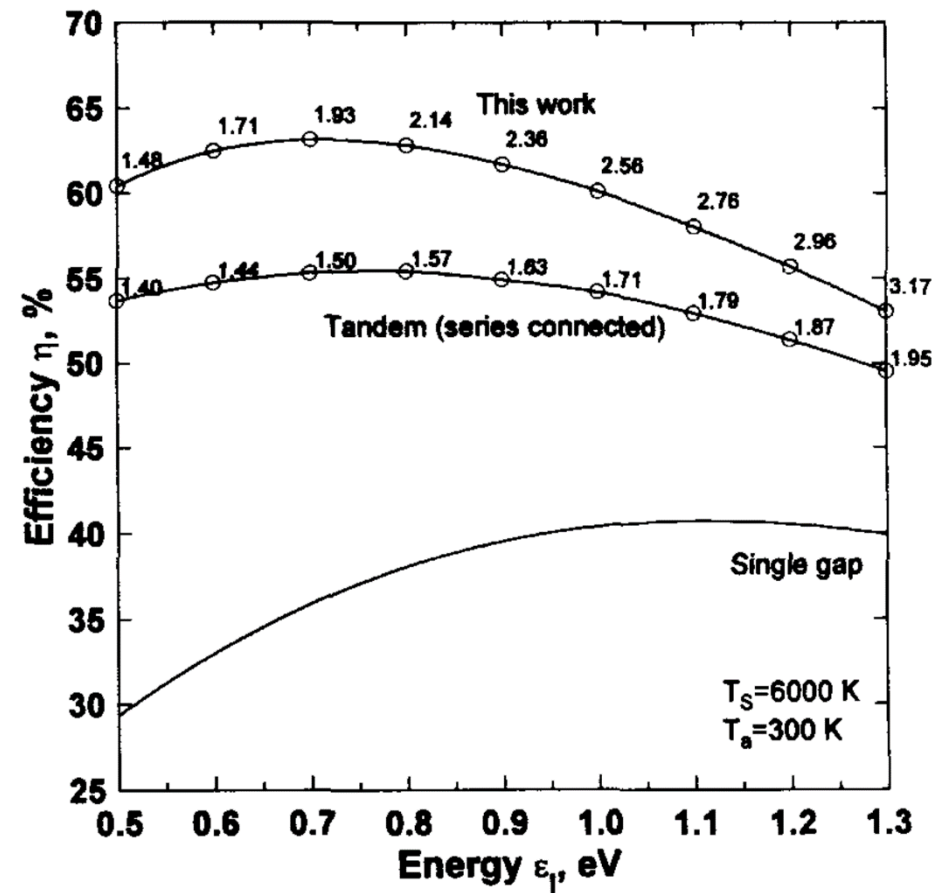
IBSC concept



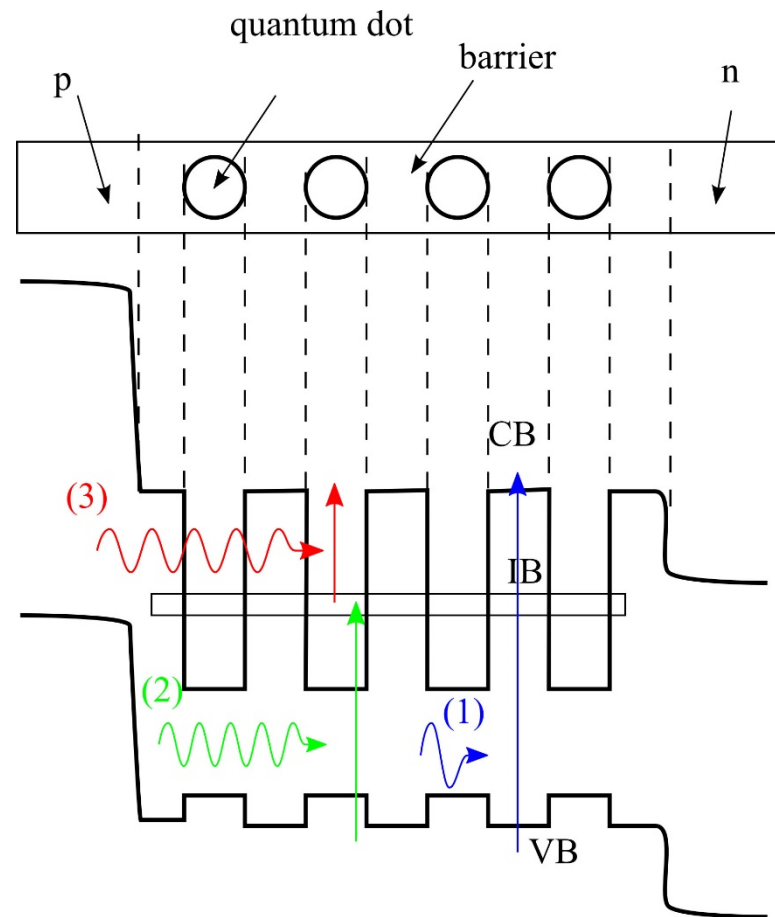
IBSC concept



Limiting efficiency

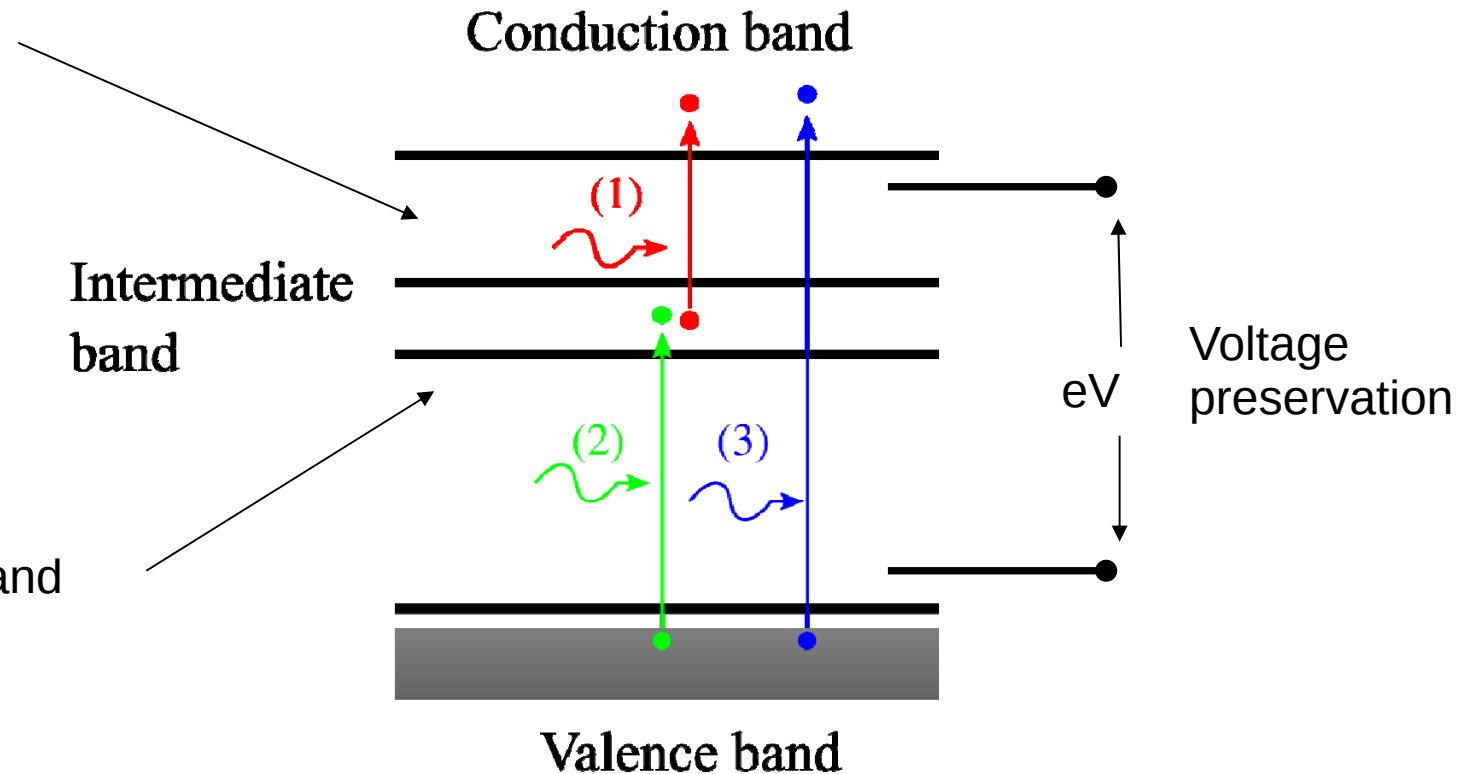


One approach for implementing the concept: QDs



Key aspects related to characterization

Two photon below
bandgap absorption



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Two-photon characterization set-up

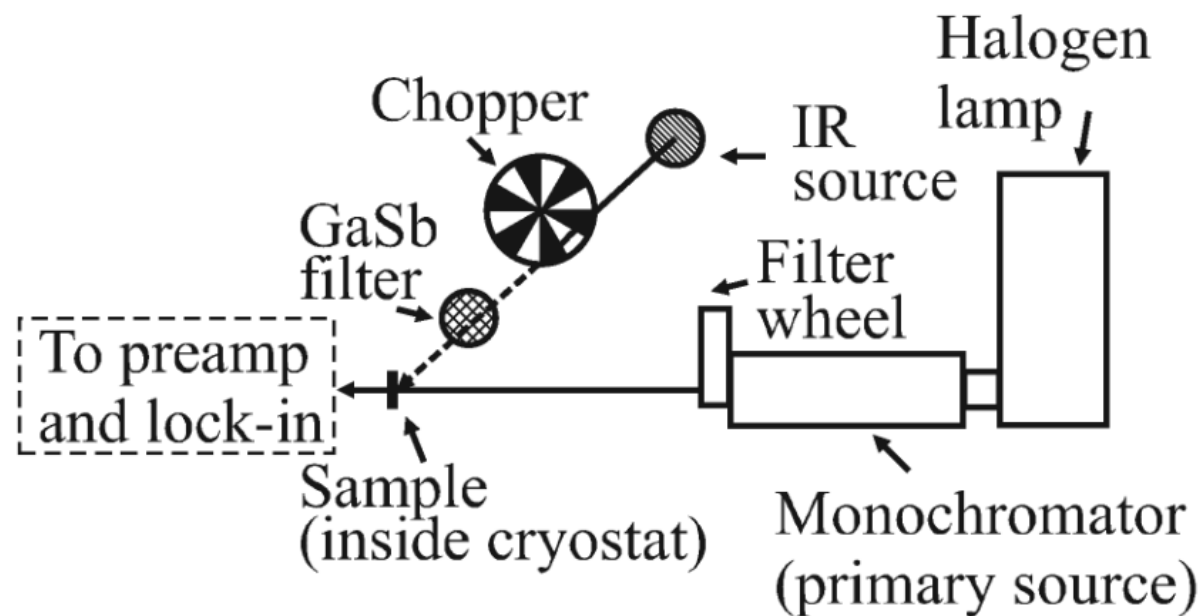
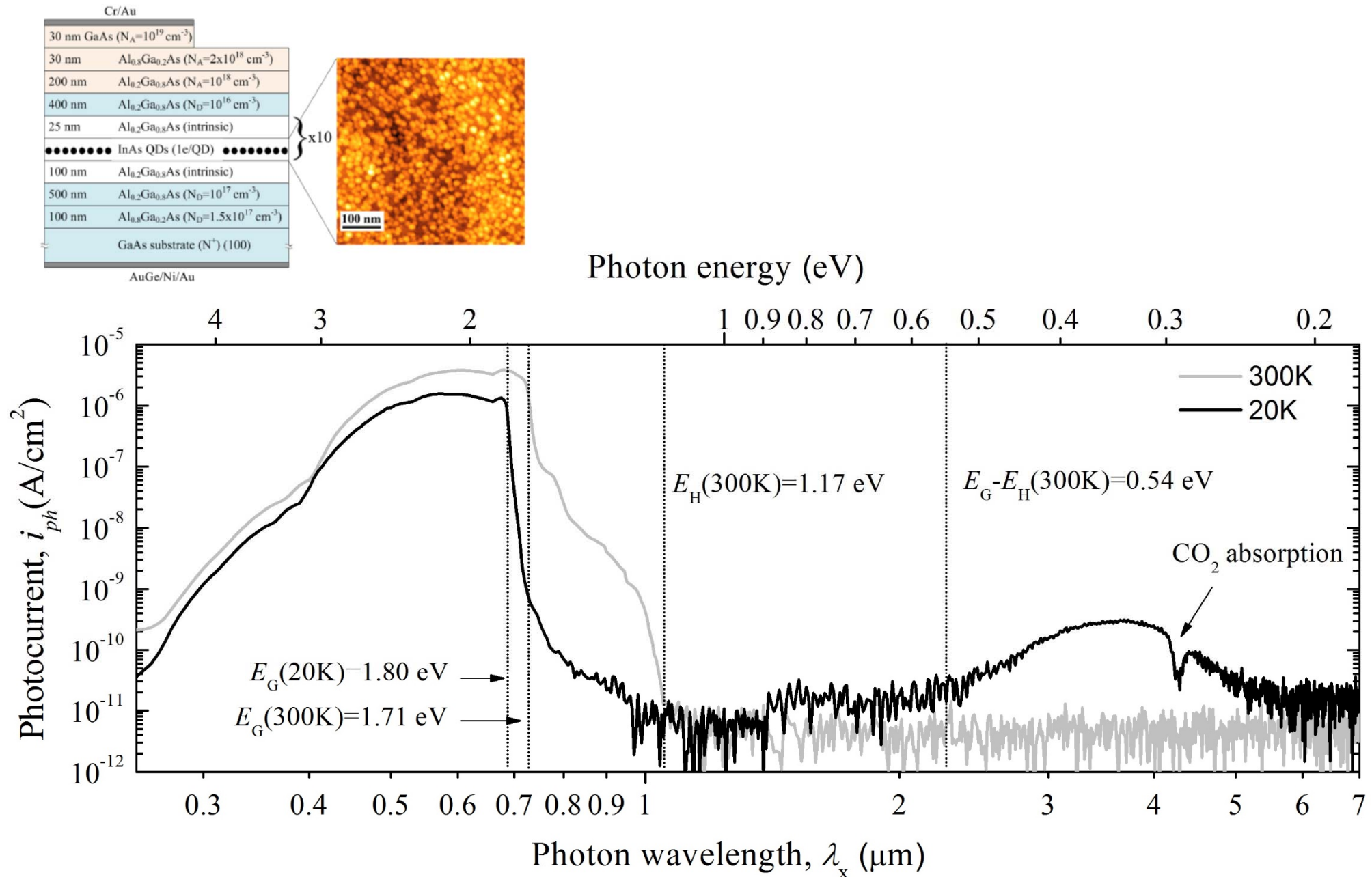


FIG. 4. Description of the experimental setup.

Some results (obtained with InAs/AlGaAs QDs)



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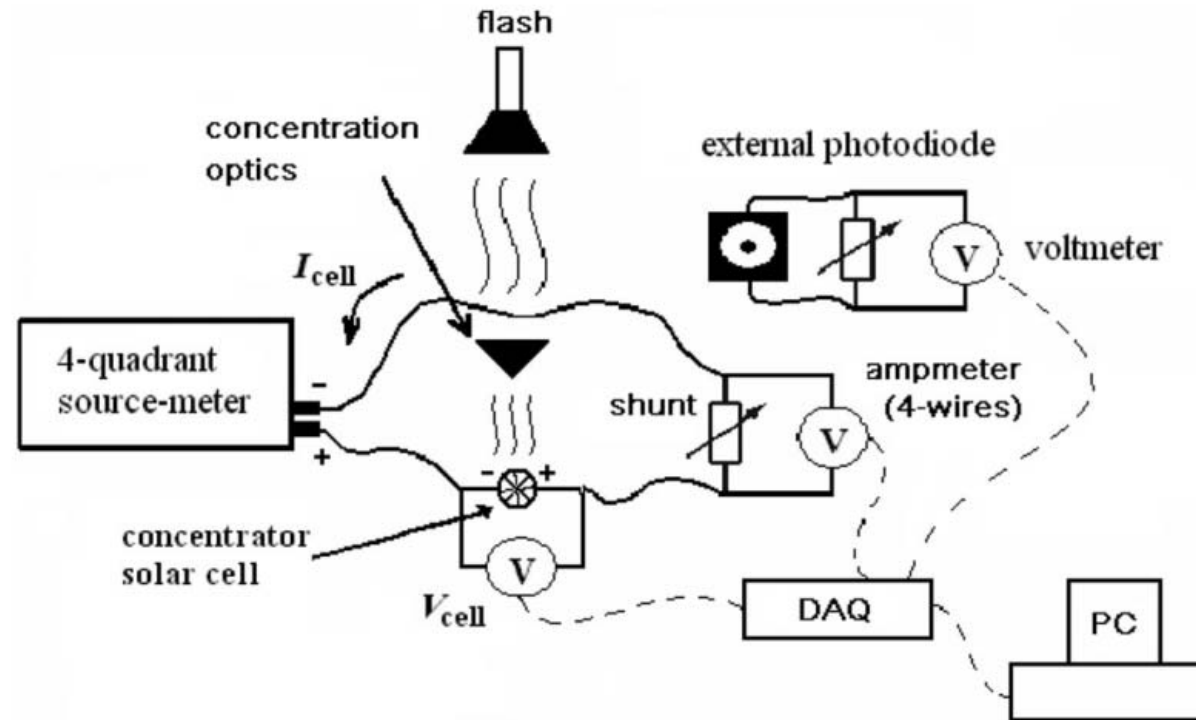
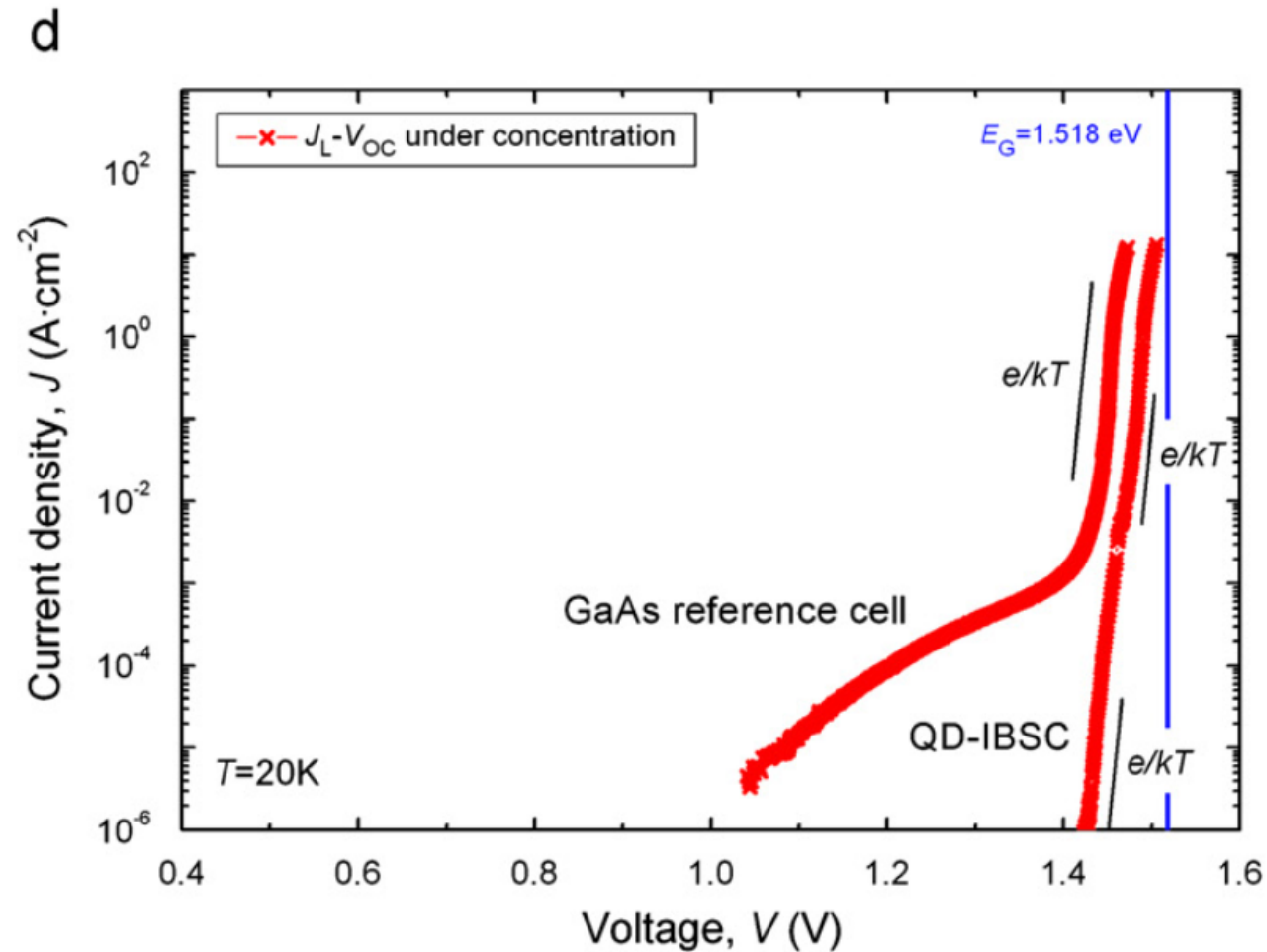


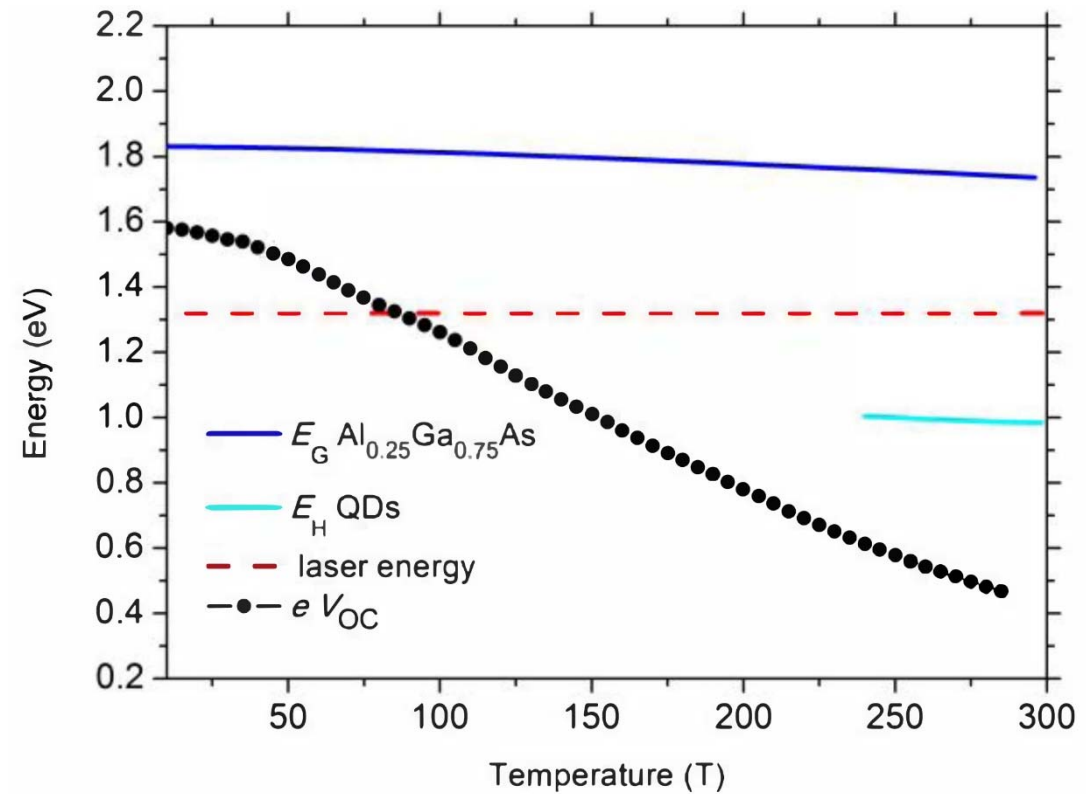
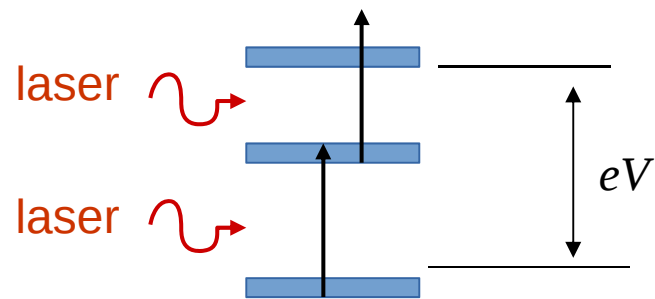
Fig. 4. Sketch of the $J_L - V_{OC}$ concentration setup.

Capability for measuring up to 5000 suns at 20 K

Some results (obtained in samples with quantum dots)



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Modulated photoreflectance

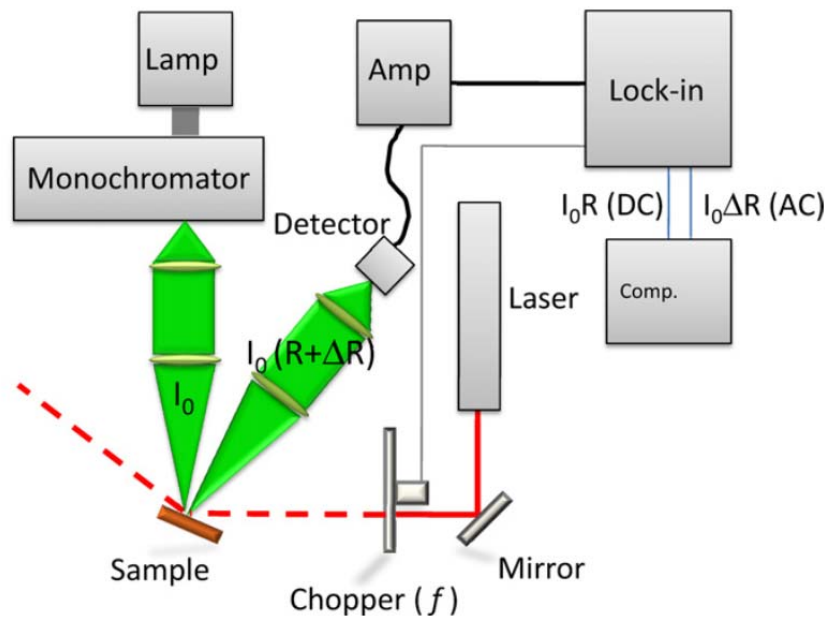
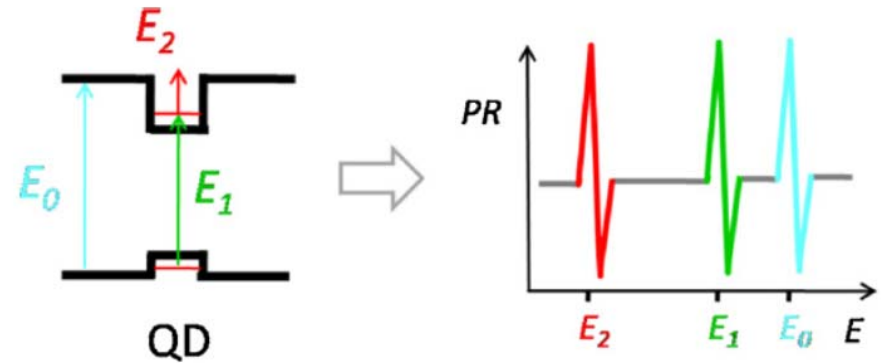
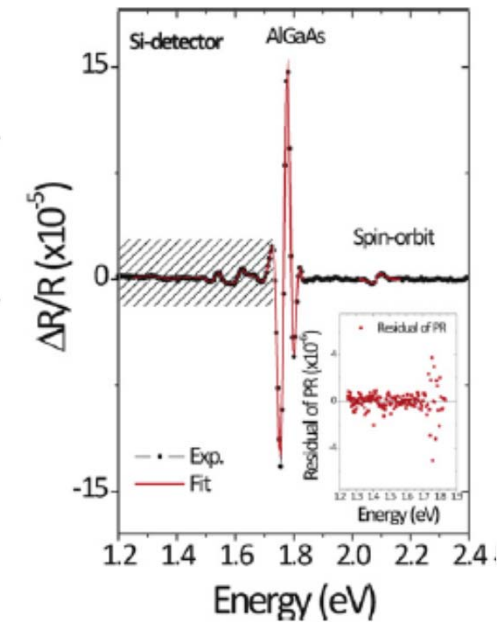


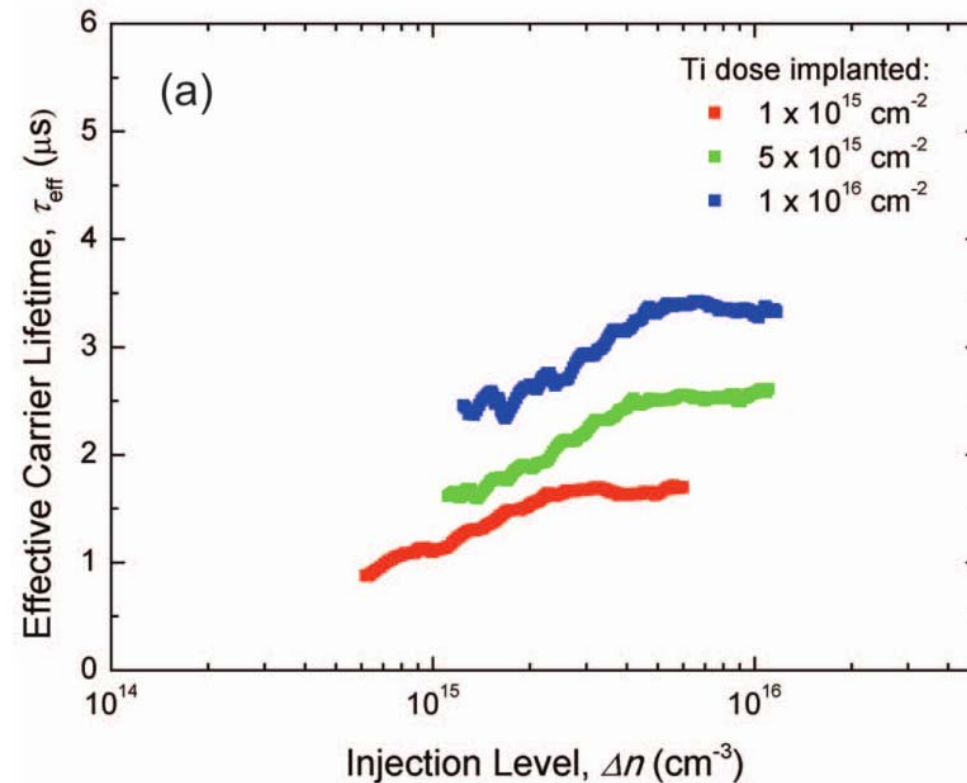
Fig. 1. Experimental setup for PR measurements.

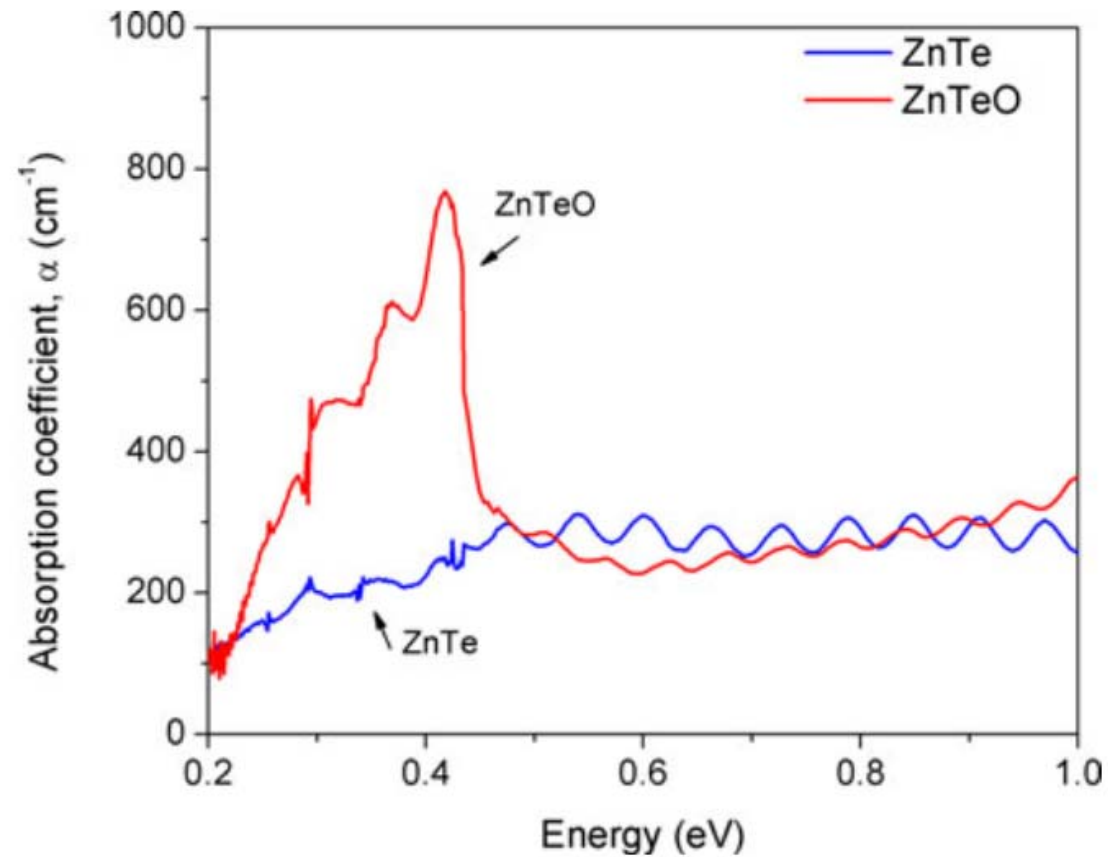


2,1 MLs InAs (0,8 nm)	x20 QDs
44 nm Al _{0,25} Ga _{0,75} As HT	
6 nm Al _{0,25} Ga _{0,75} As LT	
2 nm In _{0,2} Al _{0,2} Ga _{0,6} As	
2,1 MLs InAs (0,8 nm)	
500 nm Al _{0,25} Ga _{0,75} As	
100 nm Al _{0,40} Ga _{0,60} As	
500 nm GaAs	
GaAs substrate	



Photocoductivity decay





- Facilities to characterize below bandgap two-photon absorption (QE)
- Measurements under concentrated light up to 5000 suns and down to 20 K to check for voltage preservation
- Other techniques: PR, Photoconductivity decay, FTIR